

Power Transistors

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2SC3694

Silicon NPN Transistors

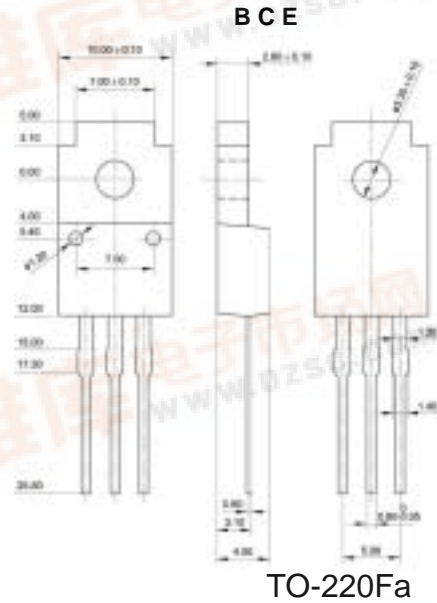


◆ Features

- . With TO-220Fa package
- . High speed ,power switching applications

◆ Absolute Maximum Ratings Tc=25

SYMBOL	PARAMETER	RATING	UNIT
V _{CB0}	Collector to base voltage	100	V
V _{CEO}	Collector to emitter voltage	60	V
V _{EBO}	Emitter to base voltage	5	V
I _C	Collector current	15	A
P _C	Collector power dissipation	30	W
T _j	Junction temperature	150	
T _{stg}	Storage temperature	-55~150	



◆ Electrical Characteristics Tc=25

SYMBOL	PARAMETER	CONDITIONS	MIN	Typ.	MAX	UNIT
I _{CB0}	Collector cut-off current	V _{CB} =60V; I _E =0			10	uA
I _{EBO}	Emitter cut-off current	V _{EB} =5V; I _C =0			10	uA
I _{CEO}	Collector cut-off current					
V _{CB0}	Collector-base breakdown voltage					
V _{CEO(SUS)}	Collector-emitter Sustaining voltage	I _C =30mA; I _B =0	60			V
V _{EBO}	Emitter-base breakdown voltage					
V _{CE(sat-1)}	Collector-emitter saturation voltages	I _C =12A; I _B =0.6A			0.5	V
V _{CE(sat-2)}	Collector-emitter saturation voltages					
h _{FE-1}	Forward current transfer ratio	I _C =3A; V _{CE} =2V	100		400	
h _{FE-2}	Forward current transfer ratio					
V _{BE(sat)1}	Base-emitter saturation voltages	I _C =12A; I _B =0.6A			1.5	V
V _{BE(sat)2}	Base-emitter saturation voltages					
f _T	Transition frequency	I _C =1A; V _{CE} =10V		120		MHz
C _{ob}	Collector Out put Capacitance	I _C =0, V _{CB} =10V f=1MHz		180		pF

